

Application Note Extending the SLG59M1693C's Maximum Operating Current Range

AN-CM-240

Abstract

This application note shows how to extend the SLG59M1693C's maximum operating current range.





Contents

Abstract	1
Contents	2
Figures	2
1 Terms and Definitions	
2 References	3
3 Introduction	4
4 Using Two SLG59M1693Cs in Parallel	4
5 Conclusions	7
Revision History	

Figures

Figure 1: Schematic Layout of Connecting Two SLG59M1693C IPSs in Parallel	4
Figure 2: RDSon vs. Temperature and VIN	5
Figure 3: PCB Layout for Using SLG59M1693C in Parallel	5
Figure 4: Turn on Operation Waveform for VIN = 2 V, CLOAD = 0.1 μ F, RLOAD = 1 Ω	6
Figure 5: Turn on Operation Waveform for VIN = 0.8 V, CLOAD = 0.1 μ F, RLOAD = 0.4 Ω	6

AN-CM-240



Extending the SLG59M1693C's Maximum Operating Current Range

1 Terms and Definitions

IPS Integrated Power Switch

2 References

[1] SLG59M1693C, Datasheet, Dialog Semiconductor

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Application Note

Revision 1.0



3 Introduction

Some applications require an IPS to deliver currents higher than 1 A. One way to address this requirement is to use an integrated power switch with higher current capability. However, such a part may occupy more PCB area or consume more power than optimal for the desired current rating. Another way to obtain higher current capability is to parallel two IPSs.

4 Using Two SLG59M1693Cs in Parallel

Parallel arrangement (Figure 1) divides the current between each IPS accordingly to its RDS_{ON}.



Figure 1: Schematic Layout of Connecting Two SLG59M1693C IPSs in Parallel

Using two IPSs in parallel lowers the overall RDS_{ON} while maintaining low current consumption when ON, for any applications up to 2 A. A typical RDS_{ON} vs. Temperature and V_{IN} for this configuration is illustrated in Figure 2.









All PCB traces have the elements of resistance, capacitance and inductance. If there were a difference in path length from the voltage source to the IPSs pads, this delta trace length would create a current imbalance. In this case, the PCB layout should be designed properly to minimize parasitic impedance and especially parasitic inductance on V_{IN} and V_{OUT} pins. Excess trace inductance may cause a delay effect during on/off operation. Figure 3 shows a recommended PCB layout for applications using two SLG59M1693Cs in parallel.



Figure 3: PCB Layout for Using SLG59M1693C in Parallel

Application Note

Revision 1.0



Typical operational waveforms of this two IPS solution are illustrated in Figure 4 and Figure 5.



Figure 4: Turn on Operation Waveform for VIN = 2 V, CLOAD = 0.1 μ F, RLOAD = 1 Ω



Figure 5: Turn on Operation Waveform for VIN = 0.8 V, CLOAD = 0.1 $\mu\text{F},$ RLOAD = 0.4 Ω

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Revision 1.0



5 Conclusions

Using SLG59M1693Cs in parallel lowers the overall RDS_{ON}, but current consumption when *on* still remains low. The difference in path length from the voltage source to the IPSs pads may create a current imbalance, so the recommended PCB layout is presented.





Revision History

Revision	Date	Description
1.0	22-Mar-2018	Initial Version



Status Definitions

Status	Definition
DRAFT	The content of this document is under review and subject to formal approval, which may result in modifications or additions.
APPROVED or unmarked	The content of this document has been approved for publication.

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